

Electrical Characteristics and Photodetect Mechanism of TiO₂/AlGaIn/GaN Heterostructure-Based Ultraviolet Detectors with Schottky Junction

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Figure S1 The optical image of a single chip and TO-46 package

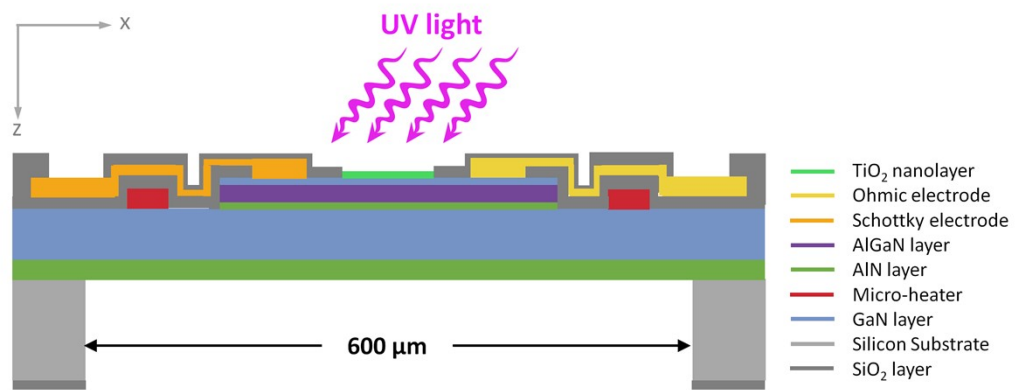


Figure S2 Schematic drawing of the cross-section of the TiO₂/AlGaN/GaN heterostructure photodetector with a Schottky junction

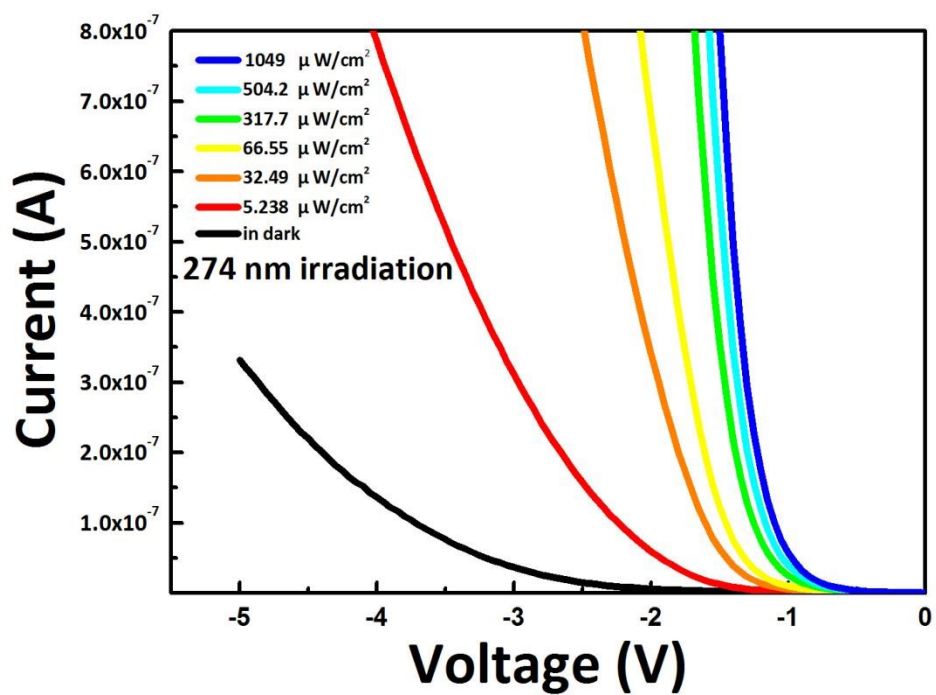


Figure S3 *I-V* characteristics of the Schottky junction-based TiO₂/AlGaIn/GaN heterostructure UV photodetector under 274 nm light illumination with different intensities of applied voltages ranging from -5 V to 0 V on a linear current scale